

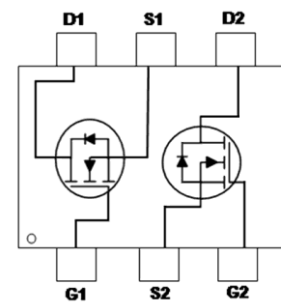
➤ General Description

This PAN0028C Dual N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- Green Device Available
- Excellent CdV/dt effect decline
- ESD Protected
- Advanced high cell density Trench technology
- TSOP-6 package design

➤ TSOP-6



➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, V_{GS} @ 10V ¹	$I_D@T_A=25^\circ C$	1.2	A
Continuous Drain Current, V_{GS} @ 10V ¹	$I_D@T_A=70^\circ C$	1	A
Pulsed Drain Current ²	I_{DM}	5	A
Total Power Dissipation ³	$P_D@T_A=25^\circ C$	1	W
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ C$
Thermal Resistance Junction-ambient ¹	$R_{\theta JA}$	125	$^\circ C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	80	$^\circ C/W$

➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	---	260	310	m Ω
		$V_{GS}=4.5V, I_D=0.5A$	---	270	320	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	μA
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V, T_J=25^\circ C$	---	---	5	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{DS}=5V, I_D=1A$	---	2.4	---	S
Total Gate Charge (10V)	Q_g	$V_{DS}=80V, V_{GS}=10V, I_D=1A$	---	9.7	---	nC
Gate-Source Charge	Q_{gs}		---	1.6	---	
Gate-Drain Charge	Q_{gd}		---	1.7	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=50V, V_{GS}=10V, R_G=3.3\Omega, I_D=1A$	---	1.6	---	ns
Rise Time	T_r		---	19	---	
Turn-Off Delay Time	$T_{d(off)}$		---	13.6	---	
Fall Time	T_f		---	19	---	
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	508	---	pF
Output Capacitance	C_{oss}		---	29	---	
Reverse Transfer Capacitance	C_{rss}		---	16.4	---	

➤ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,4}	I_S	$V_G=V_D=0V$, Force Current	---	---	1.2	A
Diode Forward Voltage ²	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150 $^\circ C$ junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

➤ Typical Characteristics

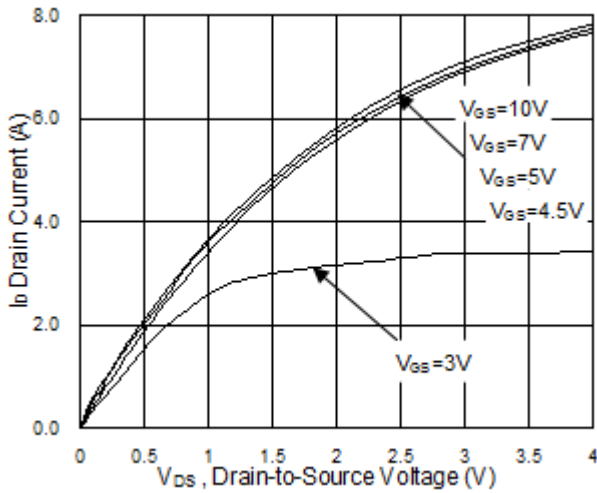


Fig.1 Typical Output Characteristics

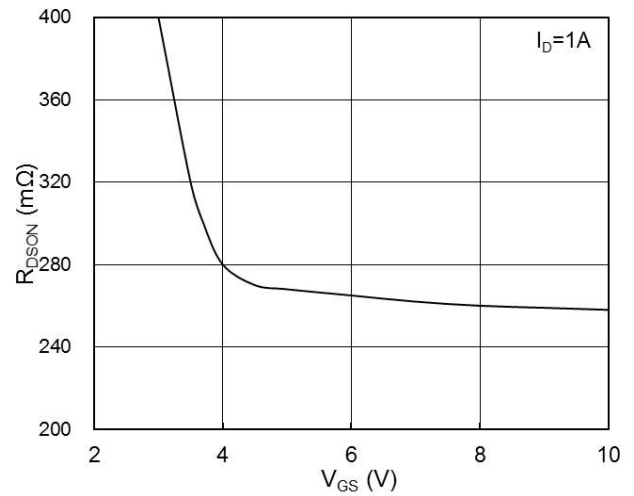


Fig.2 On-Resistance vs G-S Voltage

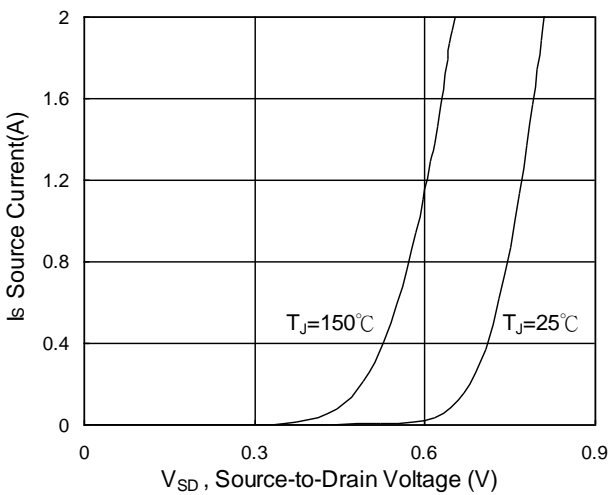


Fig.3 Source Drain Forward Characteristics

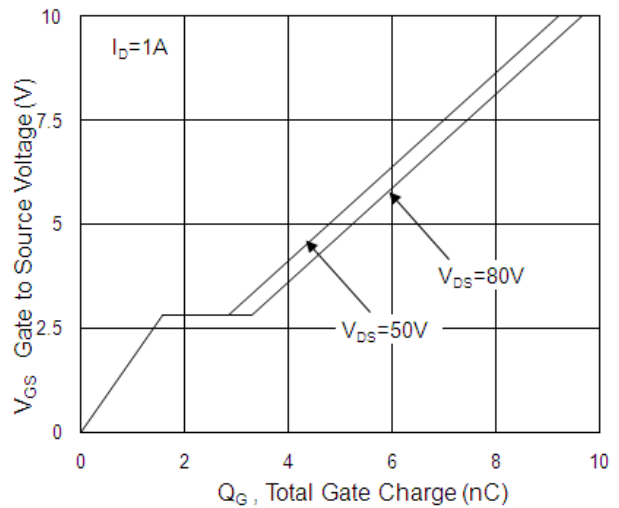


Fig.4 Gate-Charge Characteristics

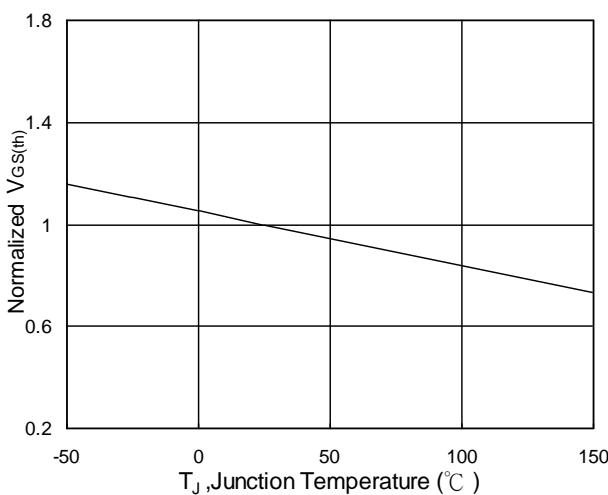


Fig.5 Normalized $V_{GS(th)}$ vs T_J

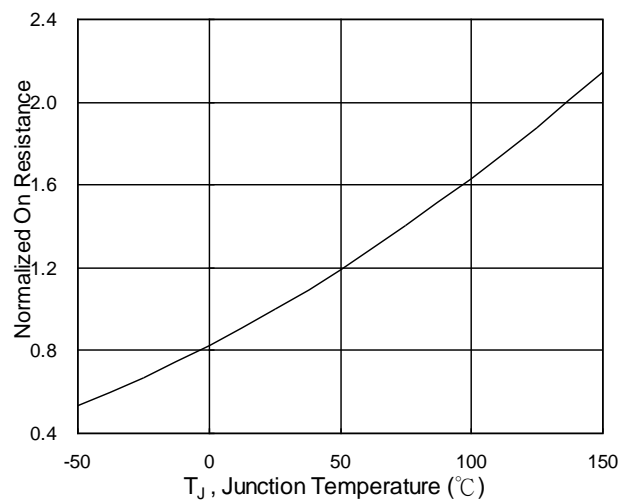


Fig.6 Normalized $R_{DS(on)}$ vs T_J

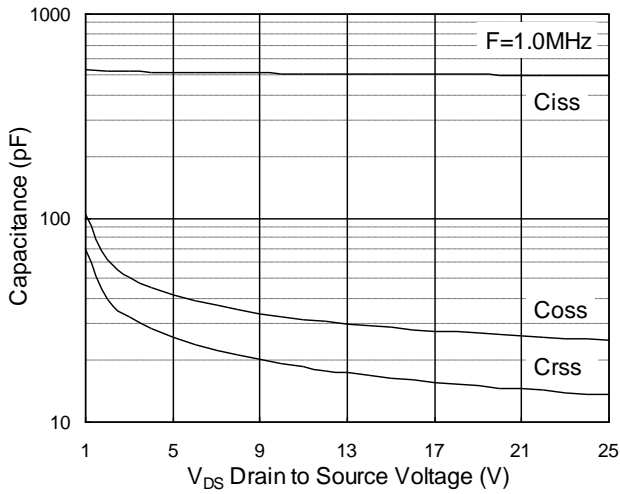


Fig.7 Capacitance

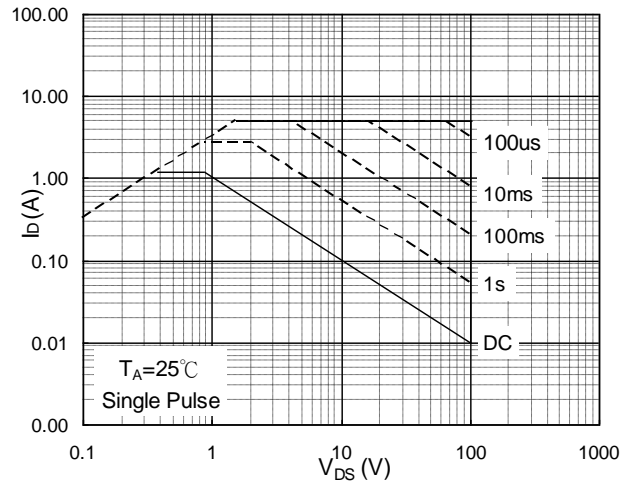


Fig.8 Safe Operating Area

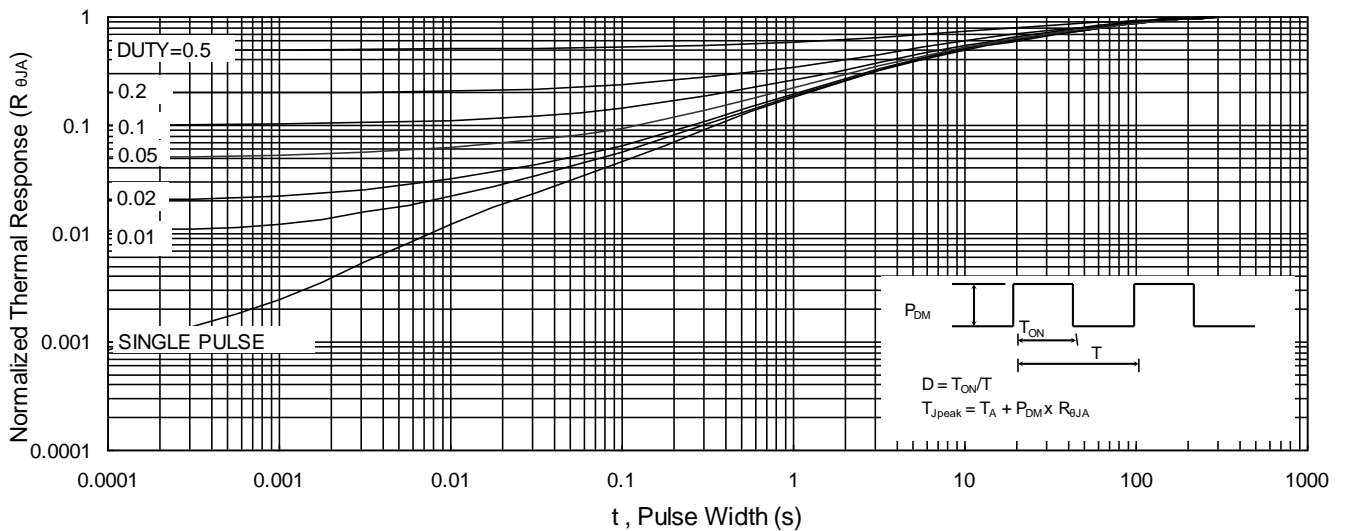


Fig.9 Normalized Maximum Transient Thermal Impedance

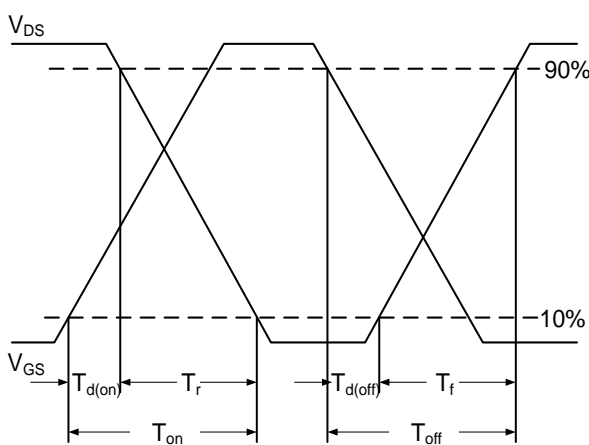


Fig.10 Switching Time Waveform

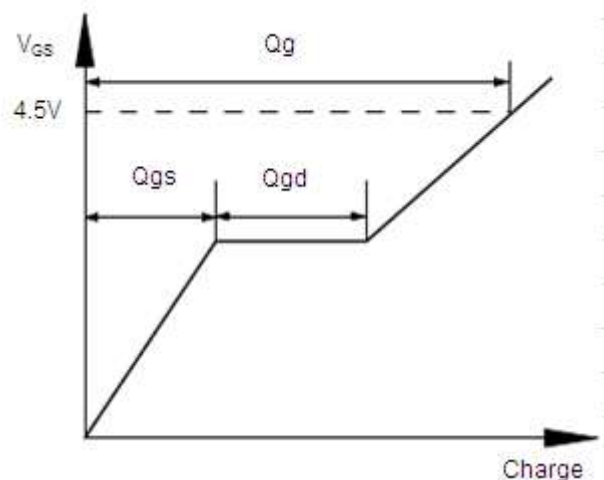


Fig.11 Gate Charge Waveform

➤ Recommand IR Reflow Soldering Thermal Profile

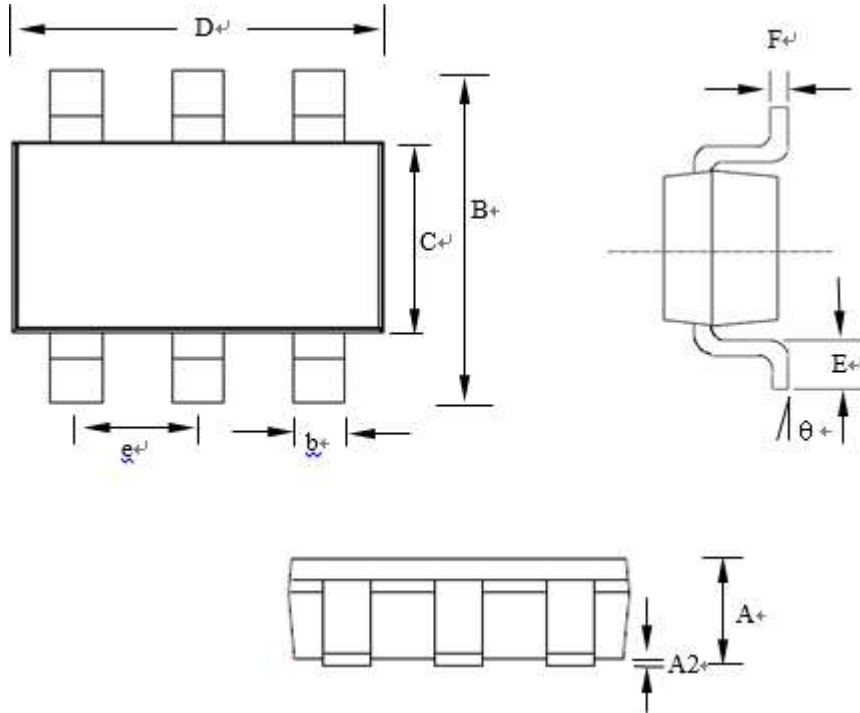


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN0028C	TSOP-6 Reel	3000 pcs

➤ Package Information (TSOP-6)



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	--	0.9	0.028	--	0.035
A2	0.00	--	0.10	0.000	--	0.004
B	2.60	2.80	3.00	0.102	0.110	0.118
C	1.40	1.60	1.80	0.055	0.063	0.071
D	2.70	2.90	3.10	0.106	0.114	0.122
E	0.30	0.40	0.60	0.012	0.016	0.024
F	0.07	0.127	0.20	0.003	0.005	0.008
b	0.30	0.40	0.50	0.012	0.016	0.020
e	--	0.95	--	--	0.037	--
θ	0°	5°	10°	0°	5°	10°

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